
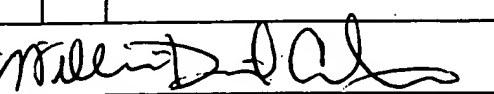


Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 32011-165642		APPLICATION NO. New Application	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT(S) Kaori TAI			
				FILING DATE August 16, 2000			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)							
		Goto et al., "Leakage Mechanism and Optimized Conditions of Co Salicide Process for Deep-Submicron CMOS Devices" IEDM Tech., Dig. 1995 IEEE, pp. 449.					
EXAMINER				DATE CONSIDERED			
				Oct 06 2001			
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							